



|  |             |     |    |
|--|-------------|-----|----|
| Average gate power dissipation ( $T_j=125$ )                         | $P_{G(AV)}$ | 0.5 | W  |
| Peak gate power  | $P_{GM}$    | 10  | W  |
| Peak pulse voltage<br>( $T_j=25$ ; non-repetitive, off-state; FIG.7) | $V_{pp}$    | 3.5 | kV |

**ELECTRICAL CHARACTERISTICS** ( $T_j=25$  unless otherwise specified)

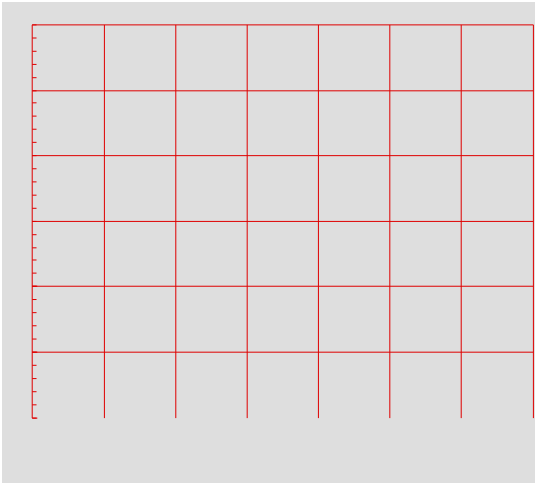
|          |                                     |     |      |     |    |
|----------|-------------------------------------|-----|------|-----|----|
|          |                                     |     |      |     |    |
| $I_{GT}$ | $V_D=12V R_L=33$                    | - - | MAX. | 10  | mA |
| $V_{GT}$ |                                     | - - | MAX. | 1   | V  |
| $V_{GD}$ | $V_D=V_{DRM} T_j=125$<br>$R_L=3.3k$ | - - | MIN. | 0.2 | V  |
| $I_L$    | $I_G=1.2I_{GT}$                     | -   | MAX. | 20  | mA |
|          |                                     |     |      | 35  |    |
| $I_H$    | $I_T=100mA$                         |     | MAX. | 20  | mA |
| dV/dt    | $V_D=540V$ Gate Open $T_j=125$      |     | MIN. | 500 |    |





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Maximum power dissipation versus RMS  
on-state current



RMS on-state current versus case  
temperature



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FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards










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